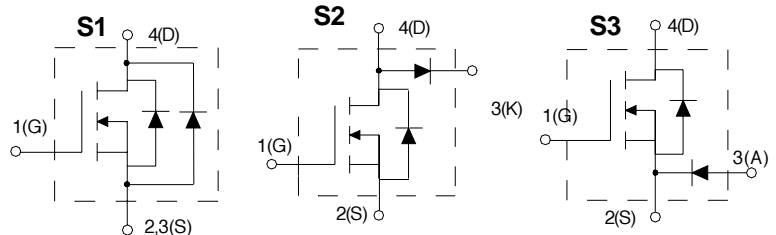


HiPerFET™ Power MOSFETs with Schottky Diodes

IXFN 100N10S1
IXFN 100N10S2
IXFN 100N10S3

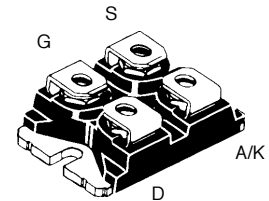
V_{DSS} = 100 V
I_{D25} = 100 A
R_{DS(on)} = 15 mΩ

Parallel, Buck & Boost Configurations
for SMPS, PFC & Motor Control Circuits



	Symbol	Test Conditions	Maximum Ratings		
HiPerFET MOSFET	V _{DSS}	T _J = 25°C to 150°C	100	V	
	V _{DGR}	T _J = 25°C to 150°C; R _{GS} = 1 MΩ	100	V	
	V _{GS}	Continuous	±20	V	
	V _{GSM}	Transient	±30	V	
	I _{D25}	T _C = 25°C	100	A	
	I _{DM}	T _C = 25°C, pulse width limited by max. T _{JM}	400	A	
	I _{AR}	T _C = 25°C	100	A	
	E _{AR}	Repetitive	45	mJ	
	dv/dt	I _S ≤ I _{DM} , -di/dt ≤ 100 A/μs, V _{DD} ≤ V _{DSS} , T _J ≤ 150°C, R _G = 2 Ω	5	V/ns	
	P _D	T _C = 25°C	360	W	
Diode	V _{RRM}		100	V	
	I _{RMS}		100	A	
	I _{FAVM}	T _C = 105°C; rectangular, d = 0.5	60	A	
	I _{FRM}	t _p < 10 μs; pulse width limited by T _J	700	A	
	(dv/dt) _{CR}		1	V/ns	
P _D	T _C = 25°C	150	W		
Case	T _J		-40 ... +150	°C	
	T _{JM}		150	°C	
	T _{stg}		-40 ... +150	°C	
	V _{ISOL}	50/60 Hz, RMS I _{ISOL} ≤ 1 mA	t = 1 min t = 1 s	2500 3000	V~ V~
	M _d	Mounting torque Terminal connection torque (M4)		1.5/13 1.5/13	Nm/lb.in. Nm/lb.in.
	Weight			30	g

miniBLOC, SOT-227 B
E153432



S = Source
G = Gate
D = Drain
A = Anode
K = Cathode

Features

- Popular Buck & Boost circuit topologies
- Low V_F Schottky diode with very small switching losses
- International standard package miniBLOC SOT-227B
- Aluminium nitride isolation
 - high power dissipation
- Isolation voltage 3000 V~
- Low R_{DS(on)} HDMOS™ process
- Rugged polysilicon gate cell structure
- Low drain-to-case capacitance (<60 pF)
 - reduced RFI

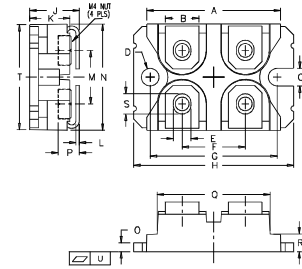
Applications

- SMPS, power factor controls and buck regulators
- DC servo and robotic drives
- DC choppers
- Switch reluctance motor controls

Advantages

- Easy to mount with 2 screws
- Space savings
- Tightly coupled Schottky diode

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$; unless otherwise specified)		
		min.	typ.	max.
V_{DS}	$V_{GS} = 0\text{ V}; I_D = 3\text{ mA}$	S1	100	V
	$V_{GS} = 0\text{ V}; I_D = 250\text{ }\mu\text{A}$	S2/S3	100	V
$V_{GS(th)}$	$V_{DS} = V_{GS}; I_D = 4\text{ mA}$		2	4 V
I_{GSS}	$V_{GS} = \pm 20\text{ V}_{DC}; V_{DS} = 0$			$\pm 100\text{ nA}$
I_{DSS}	$V_{DS} = V_{DSS}; V_{GS} = 0\text{ V}$	S1		2 mA
		S2/S3		25 μA
	$T_J = 125^\circ\text{C}$	S1		20 mA
		S2/S3		1 mA
$R_{DS(on)}$	$V_{GS} = 10\text{ V}; I_D = 0.5 I_{D25}$; Note 1			15 m Ω
g_{fs}	$V_{DS} = 10\text{ V}; I_D = 0.5 I_{D25}$; pulse test		30	45 S
C_{iss}	$V_{GS} = 0\text{ V}; V_{DS} = 25\text{ V}; f = 1\text{ MHz}$			4500 pF
C_{oss}		S1		1900 pF
		S2/S3		1600 pF
C_{rss}				870 pF
$t_{d(on)}$				30 ns
t_r	$V_{GS} = 10\text{ V}; V_{DS} = 0.5 V_{DSS}; I_D = 0.5 I_{D25}$			70 ns
$t_{d(off)}$	$R_G = 1.5\text{ }\Omega$ (External)			100 ns
t_f				30 ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}; V_{DS} = 0.5 V_{DSS}; I_D = 0.5 I_{D25}$			180 nC
Q_{gs}				36 nC
Q_{gd}				95 nC
V_{SD}	$I_F = 100\text{ A}; V_{GS} = 0\text{ V}$; Note 1 (S2, S3)			1.5 V
t_{rr}	$I_F = 25\text{ A}; -di/dt = 100\text{ A}/\mu\text{s}; V_R = 25\text{ V}$			200 ns
Q_{RM}				0.8 μC
I_{RM}				6 A
R_{thJC}				0.35 K/W
R_{thCK}				0.05 K/W

miniBLOC, SOT-227 B


M4 screws (4x) supplied

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	38.00	38.23	1.496	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.76	0.84	0.030	0.033
M	12.60	12.85	0.496	0.506
N	25.15	25.42	0.990	1.001
O	1.98	2.13	0.078	0.084
P	4.95	5.97	0.195	0.235
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.174
S	4.72	4.85	0.186	0.191
T	24.59	25.07	0.968	0.987
U	-0.05	0.1	-0.002	0.004

Schottky Diode
Characteristic Values

 ($T_J = 25^\circ\text{C}$, unless otherwise specified)

Symbol	Test Conditions	Characteristic Values		
		min.	typ.	max.
I_R	$V_R = V_{RRM}$			2 mA
	$T_J = 125^\circ\text{C}; V_R = V_{RRM}$			20 mA
V_F	$I_F = 60\text{ A}; V_{GS} = 0\text{ V}$; Note 1			0.86 V
	$I_F = 60\text{ A}; V_{GS} = 0\text{ V}$			0.73 V
	$I_F = 120\text{ A}$			0.93 V
R_{thJC}				0.8 K/W
R_{thJK}				0.1 K/W

IXYS reserves the right to change limits, test conditions, and dimensions.

 IXYS MOSFETS and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,881,106	5,017,508	5,049,961	5,187,117	5,486,715
4,850,072	4,931,844	5,034,796	5,063,307	5,237,481	5,381,025